C om plete stabilization and im provem ent of the characteristics of tunnel junctions by therm al annealing

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(D ated: M arch 23, 2024)

W e have observed that submicron sized A 14 lb_{x} (A ltunnel junctions can be stabilized completely by annealing them in vacuum at temperatures between 350 C and 450 C. In addition, low temperature characterization of the samples after the annealing treatment showed a marked improvement of the tunneling characteristics due to disappearance of unwanted resonances in the current. Charging energy, tunneling resistance, barrier thickness and height all increase after the treatment. The superconducting gap is not a ected, but supercurrent is reduced in accordance with the increase of tunneling resistance.

Submicron sized metal{insulator{metal (M IM) tunnel junctions have been used widely in applications such as radiation detectors[1], single electron transistors (SET)[2], and tunnel junction coolers and therm on eters [3]. They are also the centralelem ent in superconducting quantum bits [4, 5, 6, 7, 8], and magnetic junctions [9] are developed for memory applications. However, there are often problem swith stability of the junctions in room air conditions, the most noticable being aging, i.e. a slow ly creeping increase of the tunneling resistance R_T with tim e. Instability of the junctions is an obvious draw back when considering practical and commercial applications of tunnel junctions.

O ne possible reason for aging is the absorption of unwanted molecules into the barrier. Direct knowledge of these processes is sketchy, although it is known that vacuum conditions can slow down aging signi cantly. [10] A nother possibility is the relaxation of the oxide barrier properties. Typically, tunnel barriers in M \mathbb{M} junctions are fabricated by room temperature them alloxidation of a disordered base electrode. This procedure results in form ation of a polycrystalline or am orphous oxide layer, in which atom s are not in their global equilibrium positions. The relaxation from this "glassy" state could take months at room temperature. Moreover, in A \mathbb{D}_{x} barriers studied here, chem isorbed oxygen ions bound on the barrier surface during fabrication have also been shown to be a source of instabilities. [11]

A typical rem edy for nding a better energy m inim um is therm all annealing, the arti cial acceleration of the relaxation processes by heating up the sample for some time and then letting it cool again. For technologically important Nb/A LA D_x/Nb junctions, annealing treatments in gas atmospheres (He, N₂, Ar, air) were shown to change the barrier properties, always increasing R_T. [12, 13, 14, 15] On the other hand, for magnetic tunnel junctions, improvements in their performance were obtained with vacuum anneals. [16, 17]

In this letter we discuss how A l{A lb $_x$ {A ltunnel junctions can be completely stabilized, and their characteristics improved by therm all annealing in vacuum. The general trend of increase of R_T with the annealing is re-

produced. The bias voltage dependence of the tunneling conductance reveal that the junction characteristics become more ideal after the anneal. In addition, the charging energy, the elective barrier thickness and height all increase due to the annealing. Previous work on annealed A HA D_x -Aljunctions [18] is partly inconsistent with our results, which is not surprising, as they used a forming gas (H₂/N₂) atm osphere in their process instead of the inert vacuum used here.

A total number of 178 A lAD_x {A l sam ples were annealed, containing either a single junction or two junctions in series, fabricated by conventional electron beam (e-beam) and standard double angle vacuum evaporation techniques. A ll the junctions had either a junction area

0:05 m² or 0:15 m². All sam ples were fabricated on oxidized silicon substrates, which were usually cleaned with an oxygen plasm a just before Aldeposition. For a few samples which were not annealed, plasm a cleaning was not performed to see how the aging process is affected. The 300 nm wide and 55 nm thick Alwires were e-beam evaporated in high vacuum at a rate 0:3 nm /s, and the A D_x barriers were therm ally grown in situ in pure oxygen at 02-0:5 m bar for 3 5 m inutes. To reduce the e ects of contam ination, all sam ples were postoxidized in situ as a last step in 0:5 bar of pure oxygen for vem inutes. The samples were annealed in a vacuum chamber ($P < 10^{3}$ mbar) to temperatures ranging from 200 C to 500 C. The tem perature cycle consisted of a quick (m inutes) heating phase followed by a slow (hours) cooling cycle; details can be found in Ref. [19].

A ging wasm on itored before and after the annealing by m easuring the sam ple resistance at room tem perature vs. time, with all sam ples stored in room air. Representative results are shown in Figl. The solid and dashed lines show the typical aging of non {annealed sam ples with and without plasm a cleaning of the substrate, respectively. The two sam ples shown were fabricated in the sam e evaporation and oxidation step to ensure identical conditions. It is clear that plasm a cleaning of the substrate before A ldeposition results in signi cant reduction of aging, but does not stabilize the junctions. We conclude that som e organic contam inants, m ost likely resist

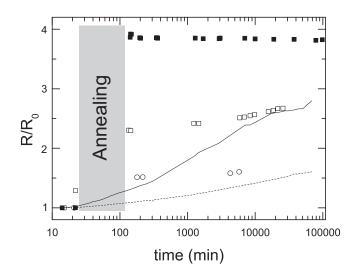


FIG.1: Aging of a non {annealed sample with (dashed) and without (solid) plasm a cleaning of the substrate. Open circles represent aging when the sample was annealed at 200 C, open squares at 300 C and lled squares at 400 C, respectively. All resistances are normalized with initial resistance at time equals zero (R_0).

residue on the substrate, are partly responsible for the aging phenom enon. The aging for a few representative annealed samples is also shown in Fig. 1, with di erent sym bols denoting di erent annealing tem peratures. The annealing process started approximately 20 m inutes after the end of fabrication, which de nes the zero of time and the initial resistance $R_0 = R$ (t = 0) for each sample. C learly, annealing tem peratures 200 C and 300 C do not lead to stabilization, whereas com plete stabilization occurs at 400 C.Note that the last datapoints correspond to tim es over twom onths after the fabrication. Com plete stabilization was also observed at annealing tem peratures 350 C and 450 C (data not shown), but 500 C always resulted in breakdown of the junctions. In addition, the therm altreatments always led to increase of the sample resistance. At 400 C, where we have the largest am ount of data (120 sam ples), the increase varied from a factor of two to a factor of eight, typically being between a factor of two to four. The range of initial R_T / junction for the 400 C treatments was from 1 k to 100 k , and no clear dependence of the R_T increase on the initial R_T was observed. Curiously, the low temperature anneals at 200 C and 300 C that did not lead to stabilization show approximately the same logarithm ic aging rate as the non-annealed sam ples, see Fig. 1, but with a jum p of the resistance caused by the treatment. This means that som e of the resistance increase is not correlated with the stabilization in any way.

For ten two junction samples, the normal state tunneling properties were characterized before and after the annealing at 400 C by measuring the tunneling current and di erential conductance dI=dV vs. bias voltage at 4.2 K with standard lock {in techniques. In this case, the

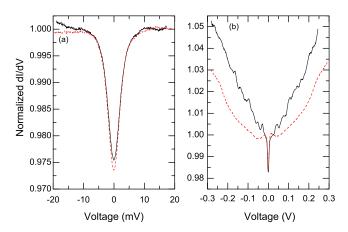


FIG.2: (Color online) A typical normalized dI=dV vs. V spectrum in units of G_T of a sample before (solid) and after (dashed, red) annealing. (a) shows a narrow bias range focusing on C oulom b blockade, while (b) displays a wide bias voltage range (tunneling spectrum).

low bias voltage regime (jv j< 20m V) provides inform ation on the charging energy, i.e. capacitance, of the junctions. The charging energy $E_c = e^2 = (2C)$, where C is total capacitance of the junctions and the island, can be obtained from the height of the zero-bias C oulom b blockade (CB) dip of dI=dV [Fig. 2 (a)] when $k_B T >> E_C$, which is the appropriate limit for our junctions at 42 K.Fortwo junctions in series, the height of the dip G and E_{C} are related by $G=G_{T} = E_{C} = (6k_{B}T)$ [3], where G_T is the tunneling conductance around V = 0 without the CB dip. Figure 2 (a) shows a typical CB dip in our samples before and after the annealing. U sually E $_{\rm C}$ increased by 5 { 10 % after the annealing, with initial $E_{\rm C}$ s ranging from 9.8 eV to 53 eV corresponding to capacitances C = $82\{1:5 \text{ ff} \cdot \text{The values of } R_T = 1=G_T\}$ increased 1:5{3 times for these samples after the annealing, varying initially from sample to sample between 9.5 k and 151 k .

In Fig. 2 (b) we plot a typical tunneling conductance spectrum (dI=dV) in a wide voltage bias range $\frac{1}{V}$ j< 300 mV. The spectrum shows many resonances (peaks) before the annealing, indicating that initially our barriers are far from perfect. These resonances are usually caused by unwanted impurities within the barrier, allowing inelastic or resonant tunneling at some specic energies [20]. A lm ost all resonances have clearly disappeared after the annealing treatment, in addition the strength of the voltage dependence has been reduced. One possibility discussed before [12] is that alum inum hydrates present in the disordered barriers dehydrate in the annealing, causing the resonances due to 0 H groups to disappear. In an idealized case, i.e. by assuming a trapezoidal barrier and that direct tunneling dom inates, the voltage dependence of the tunneling conductance is commonly parametrized in the WKB approximation as $G = G_0 [1 + \frac{1}{2} (V = V_0)^2]$, where $V_0^2 = \frac{4h^2}{p} \frac{4h^2}{2m} = (e^2 m d^2)$ and $G_0 = e^2 A^2 \frac{1}{2m} (e^2 m d^2) \exp((2d^2 m d^2) - 1)$. Here A is the junction area, $_0$ is the average barrier height and $d = (m = m)^{1-2} d_{ox}$ is the elective barrier thickness, where d_{ox} is the physical thickness and m the barrier effective mass. [20] W ithin this model we conclude that the curvature param eter V₀ increases in the annealing treatm ent. Together with the increase of E $_{\rm C}$ and R $_{\rm T}$ we can deduce that both the barrier height $_0$ as well as its effective thickness d increase with the annealing treatment. W e stress that the increase of E $_{\rm C}$ alone (decrease of C) does not guarantee that d increases, as the dielectric constant most de nitely also changes during the annealing. Sim ilar kind of changes in junction parameters have also been reported earlier at least for gas annealed Nb/Al{ A D_x {Nb junctions [13, 15]. The change in the absolute values of the barrier param eters are di cult to estim ate, as the num erous resonances in the conductance spectrum before the annealing makes thing to the model unreliable. Quadratic t to the annealed data yields the values $d = 9.5 A and_0 = 1.6 eV$ for the sample in Fig. 2.

In addition to the improved tunneling characteristics, we also observed an improvement in the Al lm quality by the treatments. This was checked by measuring the resistance of a 70 nm thick, 550 nm wide wire sample at 4.2K before and after annealing at 400 C. The resistivity decreased by 30% from 5.1 to 3.4 cm, corresponding to an increase in mean free path from 7.7 nm to 12 nm. High resolution SEM images of the lm were also taken before and after the annealing, without any noticeable di erence in the lm grain structure.

In addition to measurements at 4.2 K, we also determ ined the superconducting properties of six unshunted single junction samples, cooled to below 100 mK in a dilution refrigerator. A representative I-V characteristic before and after annealing at 400 C is presented in Fig 3 (a). The increase of R_T is apparent as the decrease of the slope at high bias, in this sam ple approxim ately a factor of three. The superconducting gap was determined from the curves, with the maxim a of the dI=dV giving 2, whose value did not change after the annealing. Reduction of the critical current I_c around zero bias is also visible, as expected from the Am begaogar (Barato relation, [2] where $I_C R_T = \text{const for a constant} = .$ To study the supercurrent branch m ore accurately, we measured the switching currents by the cum ulative histogram m ethod, where a set of current pulses of constant height I_p were fed through the sample at a frequency 100 Hz and a duty cycle 5 %, and the time dependent voltage response was measured. By counting how often the junction switched to the nite voltage state at a particular I_p, the switching probability distribution of the sam ple is directly determined. Fig. 3 (b) shows the obtained results for the sample whose IV data is shown in Fig. 3 (a). It is clear that the switching current I_S (de ned as the value where the probability = 0.5) is reduced to approximately one fit of the initial value, while the width of the distribution also decreases.

By calculating the uctuation free critical current I_C

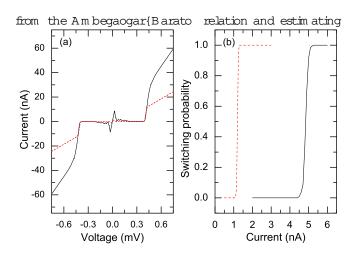


FIG.3: (Coloronline) (a) Typical IV curve and (b) switching probability characteristics of a superconducting single junction sample before (solid) and after (dashed, red) annealing m easured at 80 m K.

the capacitance of the junction as half of the capacitance measured for the two junction samples of the same junction size, the ratio of the Josephson coupling energy $E_{\rm J}$ and the charging energy $E_{\rm C}$ can be estimated to be $E_{\rm J}=\!E_{\rm C}$ 1.8. This means that the samples are in the underdam ped regime, where for unshunted junctions the prediction is that $I_{\rm S}$ / $R_{\rm T}^{3=2}$. [21] The size of reduction in the switching current $I_{\rm S}$ is therefore fully consistent with the increase in $R_{\rm T}$.

In conclusion, A HA 10 x-A 1 tunnel junctions can be completely stabilized against aging by vacuum annealing at 350 450 C . This is an obvious advantage, when considering practical and com m ercial applications of tunnel junction devices. The improvement of the tunneling characteristics was also apparent as unwanted resonances disappeared after the treatment. A nnealing led to a consistent reduction of junction capacitance and tunneling conductance for all samples studied, caused by an increase in the barrier height and thickness. Engineering these sample parameters in a controlled way by therm al vacuum annealing was not yet possible, partly because the microscopic understanding of the processes taking place is unclear. One possible application for the annealing is to increase the sensitivity of Josephson junction threshold current detectors, currently used for example in superconducting quantum bit readouts [6] or in shotnoise measurements. [22] W ith annealing, a reduction of the critical current can be achieved without a significant reduction of the capacitance, which decreases the sensitivity. [23]

We thank J.M annik for discussions. This work has been supported by the A cadem y of F in land projects N o. 105258 and 205476 (TULE program). PJK.acknowledgesNationalG raduate Schoolin M aterials Physics and Em ilA altonen Foundation for partial nancial support.

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